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Date Submitted: March 7, 2005

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Sheet 1 of 1 Attorney Docket Number 017700-0174

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
	A1	2004/0224851	A	KAKIMOTO et al.	11-11-2004	
	A2	6,743,533	B1	KAKIMOTO et al.	06-01-2004	
	A3	5,687,899		YOSHIDA et al.	03-04-1997	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
	A4	JP	2000-299026		FUJIKURA LTD.	10-24-2000		A
	A5	JP	07-291626		SUMITOMO ELECTRIC IND. LTD.	11-07-1995		A

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>6</sup>
	A6	"Material Engineering for Studying with Personal Computer," The 2001 Seminar of Japan Institute of Metals, November 2001, pp. 21-31.	
	A7	K. HASEGAWA et al., "Preparation of SmBa <sub>2</sub> Cu <sub>3</sub> O <sub>y</sub> Films With Improved In-plane Alignment," J. Japan Inst. Metal., Vol. 66, 2002, pp. 320-328.	
	A8	M. NAKAMURA et al., "Fabrication of Single Crystal of SmBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> by the Modified Top-Seeded Solution Growth Method in Low Oxygen Partial Pressure Atmosphere, Japan J. of Applied Phys., Vol. 34, 1995, pp. 6031-6035.	
	A9	T. MURATA et al., "Interface Structures in NdBCO/MgO and YBCO/MgO Superconducting Films Grown by LPE Method," The Fourth Pacific Rim International Conference of Advanced Materials and Processing, 2001, pp. 729-732, The Japan Institute of Metals.	
	A10	K. SUDOH et al., "Superconducting properties and surface morphology of SmBa <sub>2</sub> Cu <sub>3</sub> O <sub>6+δ</sub> thin films," Physica C, Vol. 357-360, 2001, pp. 1358-1360; Elsevier Science.	
	A11	Y. WU et al., "Atomic configurations of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> /MgO interfaces," Physica C 371, 2002, pp. 309-314, Elsevier Science.	
		DUPLICATE OF 08/03/2005	

Examiner Signature

/Kallambella Vijayakumar/

Date Considered

03/25/2008

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